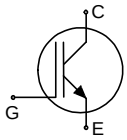
IGD06N60T

TRENCHSTOP™ Series

Low Loss IGBT: IGBT in TRENCHSTOP™ and Fieldstop technology

Features:
- Very low $V_{CE(sat)}$ 1.5 V (typ.)
- Maximum Junction Temperature 175°C
- Short circuit withstand time 5µs
- TRENCHSTOP™ and Fieldstop technology for 600V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
- Low EMI
- Qualified according to JEDEC[1] for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : http://www.infineon.com/igbt/





PG-TO252-3 (D-PAK)

Applications:
- Variable Speed Drive for washing machines and air conditioners
- Buck converters

Type	V_{CE}	$I_{C;Tc=100°C}$	$V_{CE(sat),Tj=25°C}$	$T_{j,max}$	Marking	Package
IGD06N60T	600V	6A	1.5V	175°C	G06T60	PG-TO252-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j \geq 25°C$	V_{CE}	600	V
DC collector current, limited by T_{jmax} $T_C = 25°C$ $T_C = 100°C$	I_C	 12 6	A
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	18	
Turn off safe operating area, $V_{CE} = 600V$, $T_j = 175°C$, $t_p = 1µs$	-	18	
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time[2)] $V_{GE} = 15V$, $V_{CC} \leq 400V$, $T_j \leq 150°C$	t_{SC}	5	µs
Power dissipation $T_C = 25°C$	P_{tot}	88	W
Operating junction temperature	T_j	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	
Soldering temperature reflow soldering, MSL1		260	

[1] J-STD-020 and JESD-022
[2)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		1.7	K/W
Thermal resistance, junction – ambient	R_{thJA}		62	

Electrical Characteristic, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V, I_C=0.25mA	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE} = 15V, I_C=6A				
		T_j=25°C	-	1.5	2.05	
		T_j=175°C	-	1.8		
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C=0.18mA, V_{CE}=V_{GE}	4.1	4.6	5.7	
Zero gate voltage collector current	I_{CES}	V_{CE}=600V, V_{GE}=0V				µA
		T_j=25°C	-	-	40	
		T_j=175°C	-	-	700	
Gate-emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE}=20V, I_C=6A	-	3.6	-	S
Integrated gate resistor	R_{Gint}		none			Ω
Dynamic Characteristic						
Input capacitance	C_{iss}	V_{CE}=25V,	-	368	-	pF
Output capacitance	C_{oss}	V_{GE}=0V,	-	28	-	
Reverse transfer capacitance	C_{rss}	f=1MHz	-	11	-	
Gate charge	Q_{Gate}	V_{CC}=480V, I_C=6A V_{GE}=15V	-	42	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7	-	nH
Short circuit collector current[1)]	$I_{C(SC)}$	V_{GE}=15V, t_{SC}≤5µs V_{CC} = 400V, T_j = 25°C	-	55	-	A

[1)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at T_j=25 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=25°C, V_{CC}=400V, I_C=6A, V_{GE}=0/15V, r_G=23Ω, L_σ=60nH, C_σ=40pF L_σ, C_σ from Fig. E Energy losses include "tail" and diode reverse recovery. Diode used IDP06E60	-	9	-	ns
Rise time	t_r		-	6	-	
Turn-off delay time	$t_{d(off)}$		-	130	-	
Fall time	t_f		-	58	-	
Turn-on energy	E_{on}		-	0.09	-	mJ
Turn-off energy	E_{off}		-	0.11	-	
Total switching energy	E_{ts}		-	0.2	-	

Switching Characteristic, Inductive Load, at T_j=175 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=175°C, V_{CC}=400V, I_C=6A, V_{GE}=0/15V, r_G= 23Ω L_σ=60nH, C_σ=40pF L_σ, C_σ from Fig. E Energy losses include "tail" and diode reverse recovery. Diode used IDP06E60	-	9	-	ns
Rise time	t_r		-	8	-	
Turn-off delay time	$t_{d(off)}$		-	165	-	
Fall time	t_f		-	84	-	
Turn-on energy	E_{on}		-	0.14	-	mJ
Turn-off energy	E_{off}		-	0.18	-	
Total switching energy	E_{ts}		-	0.335	-	

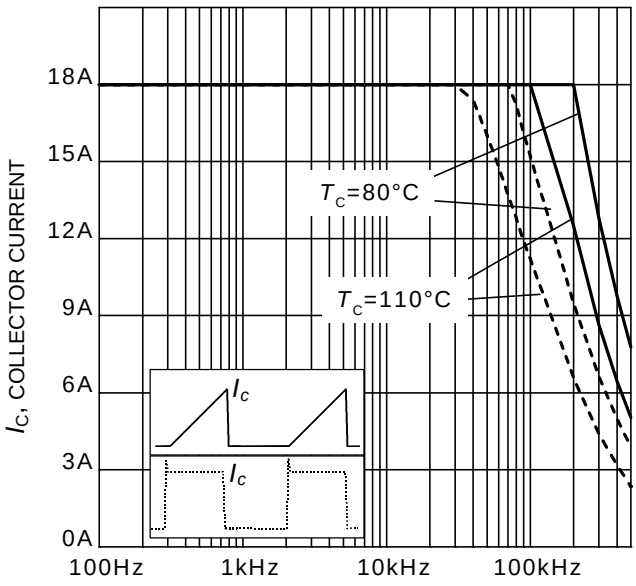


Figure 1. Collector current as a function of switching frequency
($T_j \leq 175°C$, $D = 0.5$, $V_{CE} = 400V$, $V_{GE} = 0/15V$, $r_G = 23\Omega$)

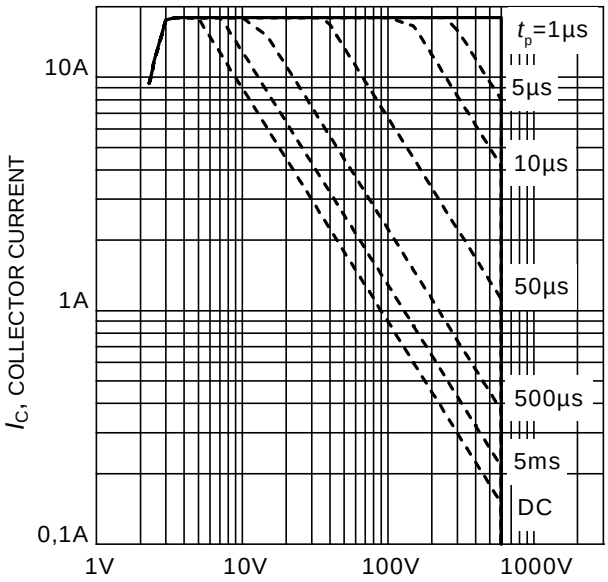


Figure 2. Safe operating area
($D = 0$, $T_C = 25°C$, $T_j \leq 175°C$; V_{GE}=0/15V)

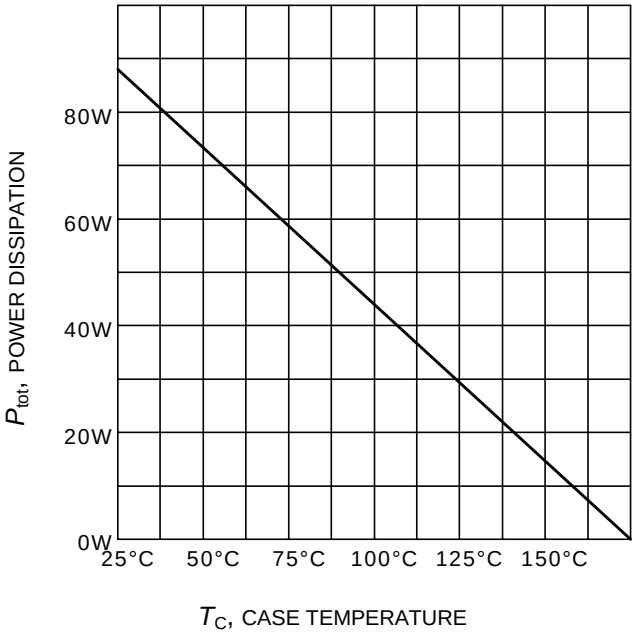


Figure 3. Power dissipation as a function of case temperature
($T_j \leq 175°C$)

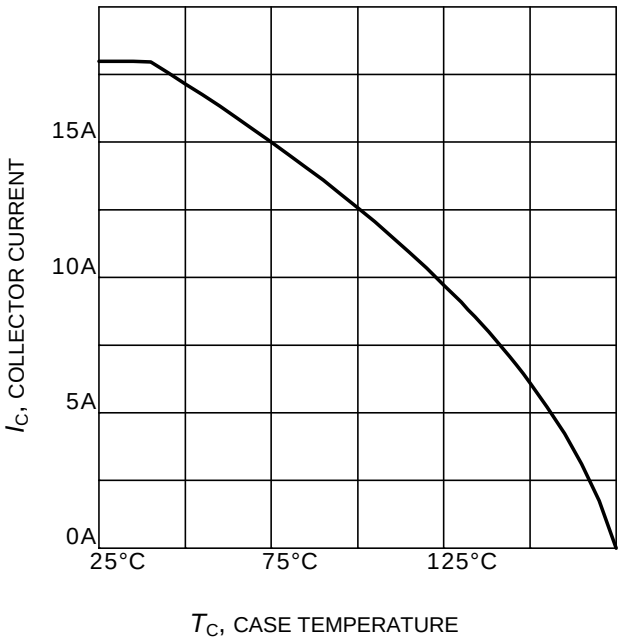


Figure 4. Collector current as a function of case temperature
($V_{GE} \geq 15V$, $T_j \leq 175°C$)

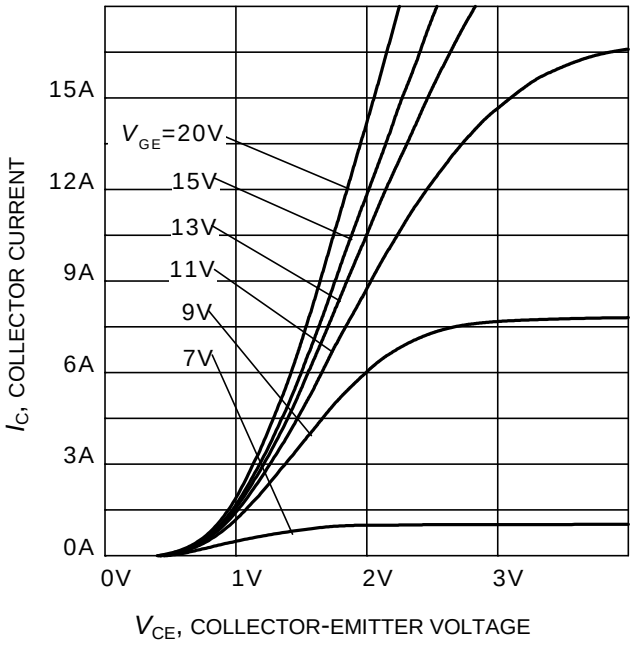


Figure 5. Typical output characteristic
(T_j = 25°C)

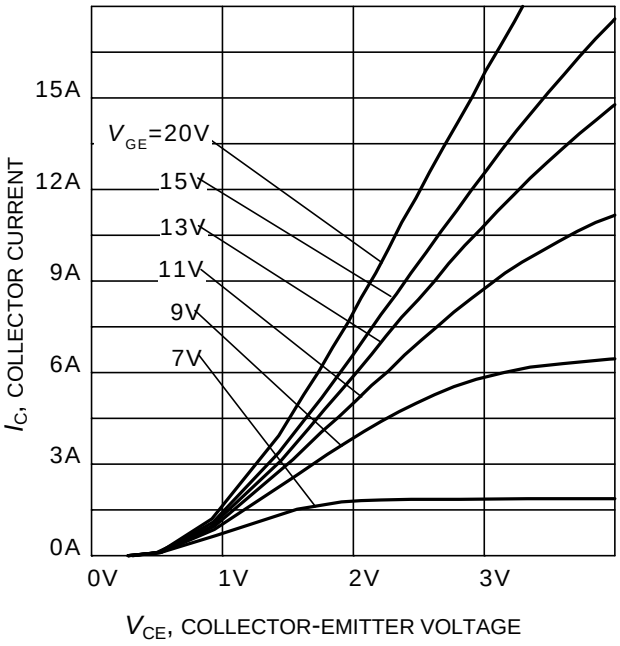


Figure 6. Typical output characteristic
(T_j = 175°C)

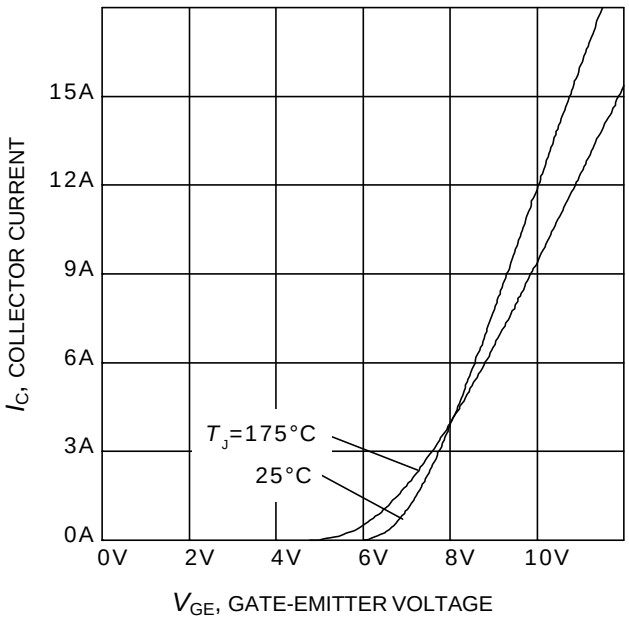


Figure 7. Typical transfer characteristic
(V_{CE}=20V)

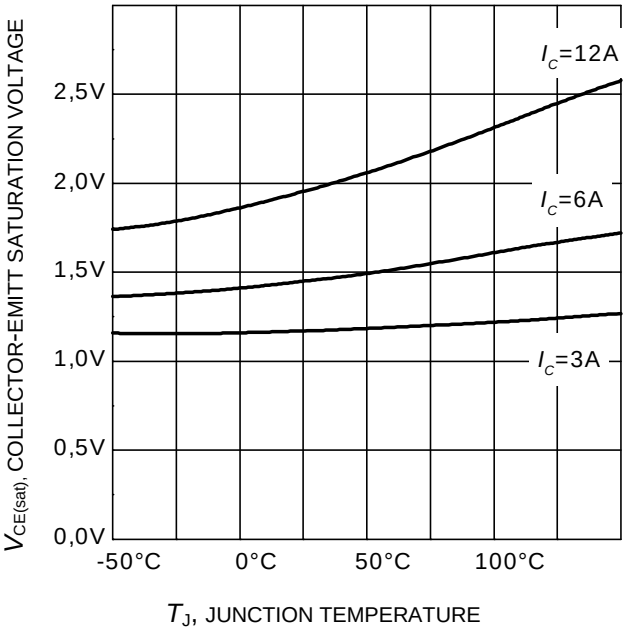


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE} = 15V)

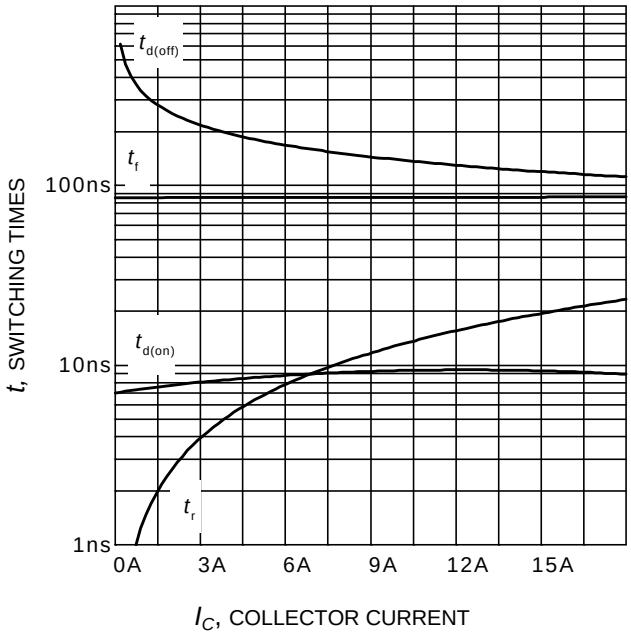


Figure 9. Typical switching times as a function of collector current
(inductive load, T_J=175°C,
V_{CE} = 400V, V_{GE} = 0/15V, r_G = 23Ω,
Dynamic test circuit in Figure E)

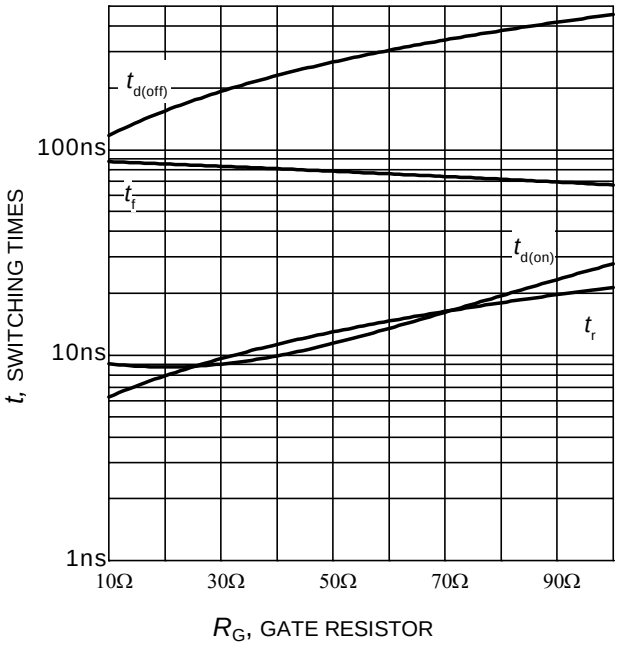


Figure 10. Typical switching times as a function of gate resistor
(inductive load, T_J=175°C,
V_{CE} = 400V, V_{GE} = 0/15V, I_C = 6A,
Dynamic test circuit in Figure E)

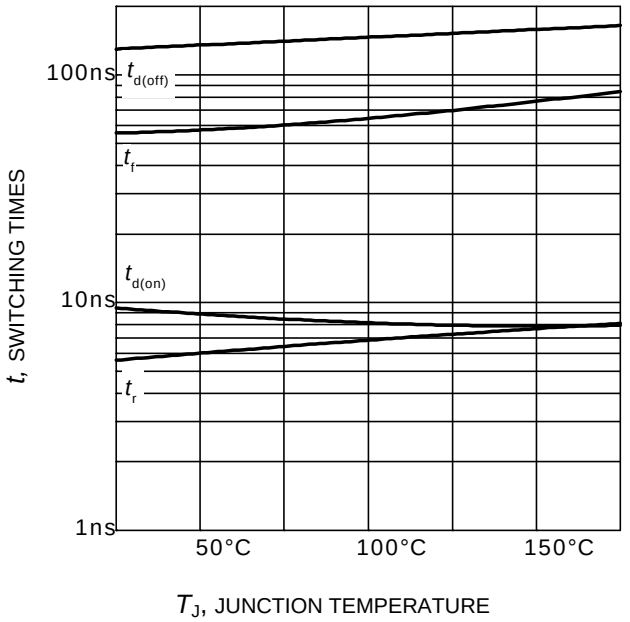


Figure 11. Typical switching times as a function of junction temperature
(inductive load, V_{CE} = 400V,
V_{GE} = 0/15V, I_C = 6A, r_G = 23Ω,
Dynamic test circuit in Figure E)

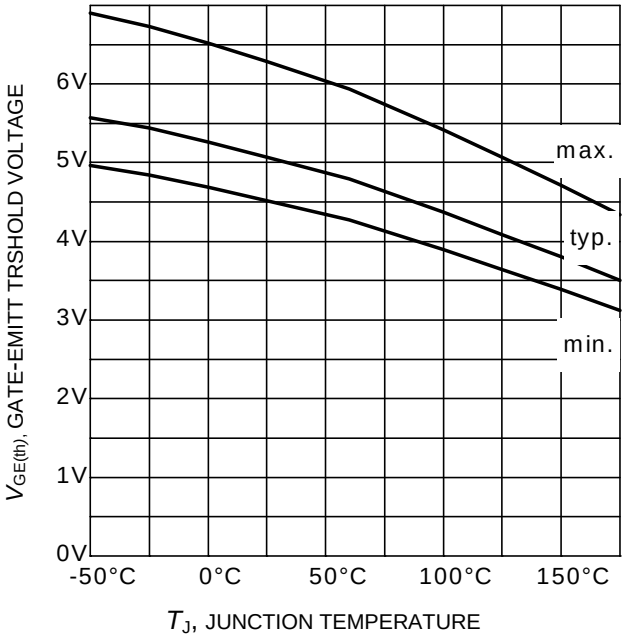


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
(I_C = 0.18mA)

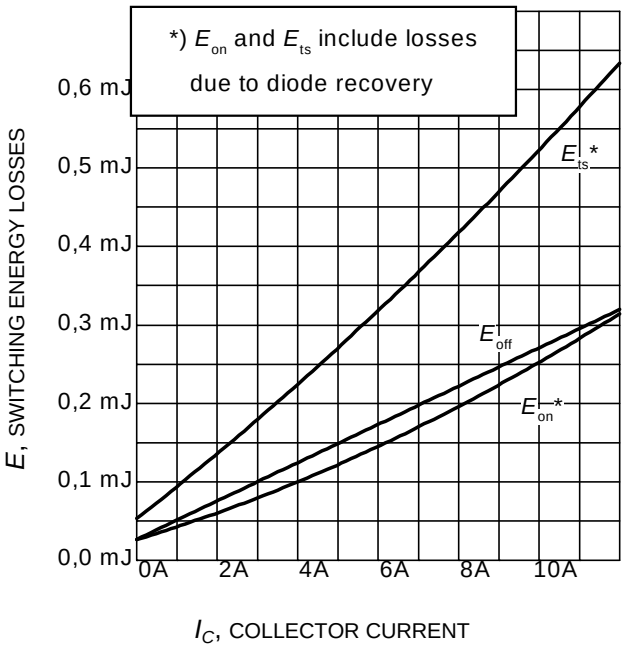


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, T_J=175°C, V_{CE}=400V, V_{GE}=0/15V, r_G=23Ω, Dynamic test circuit in Figure E)

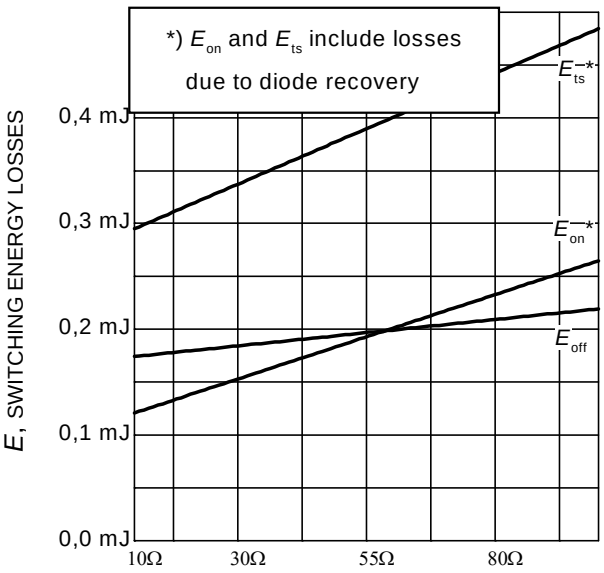


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, T_J=175°C, V_{CE} = 400V, V_{GE} = 0/15V, I_C = 6A, Dynamic test circuit in Figure E)

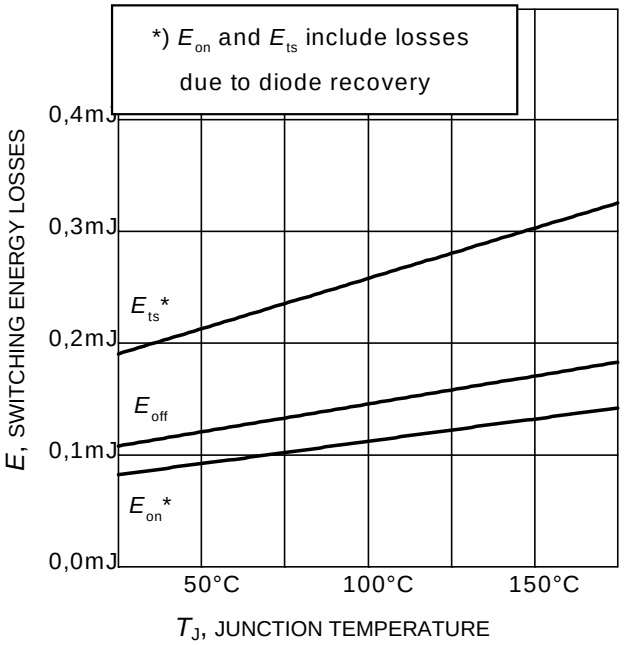


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, V_{CE}=400V, V_{GE} = 0/15V, I_C = 6A, r_G = 23Ω, Dynamic test circuit in Figure E)

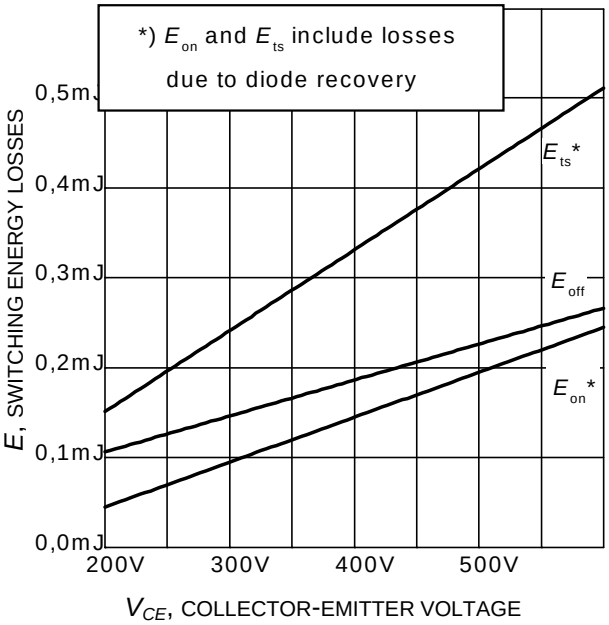


Figure 16. Typical switching energy losses as a function of collector emitter voltage
(inductive load, T_J = 175°C, V_{GE} = 0/15V, I_C = 6A, r_G = 23Ω, Dynamic test circuit in Figure E)

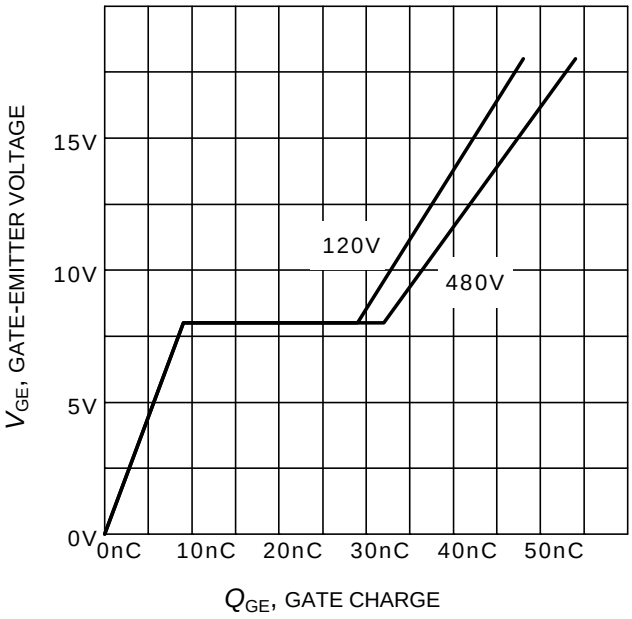


Figure 17. Typical gate charge
(I_C = 6 A)

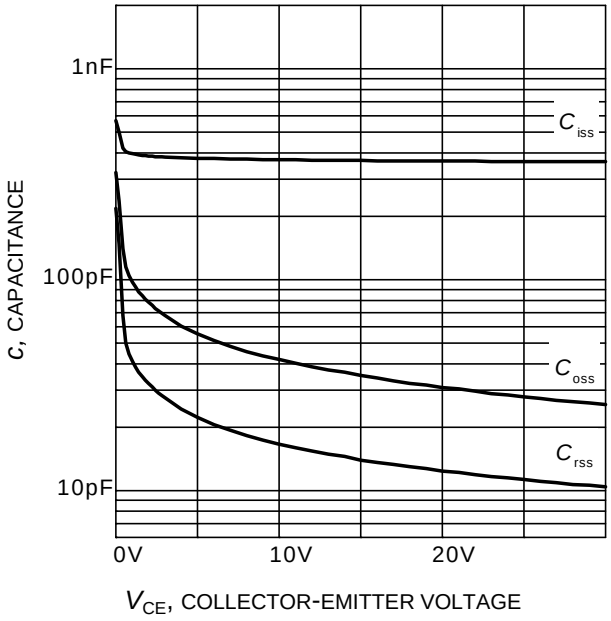


Figure 18. Typical capacitance as a function of collector-emitter voltage
(V_{GE}=0V, f = 1 MHz)

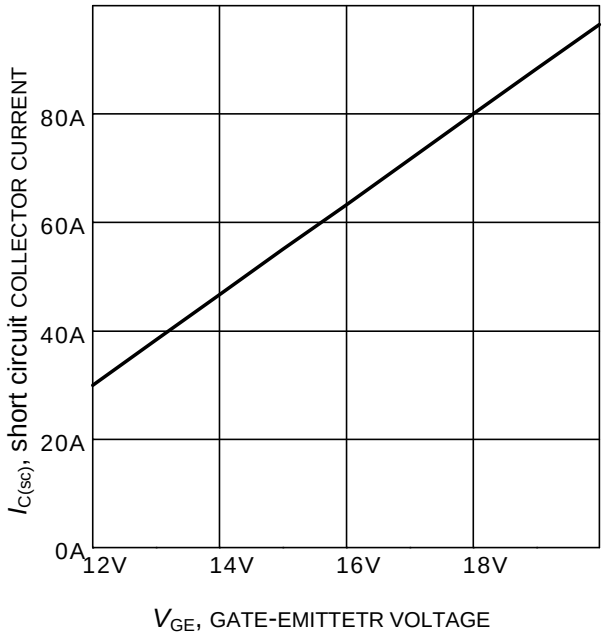


Figure 19. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \le$ 400V, $T_j \le$ 150°C)

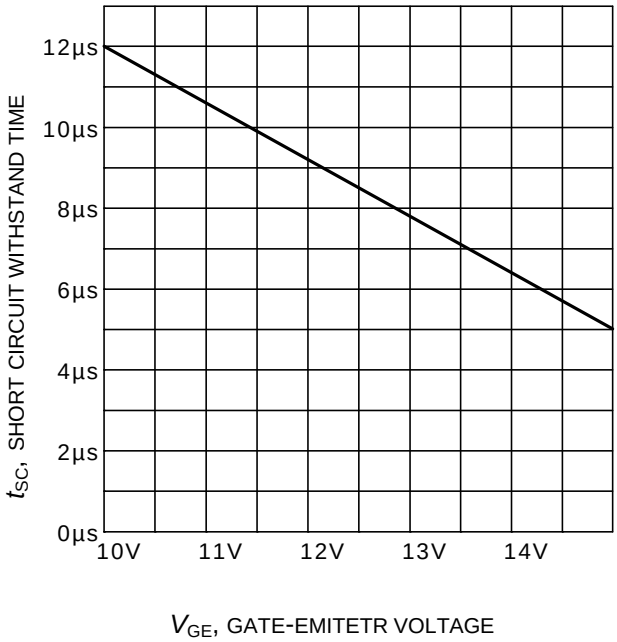


Figure 20. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE}=400V, start at T_J=25°C, T_{Jmax}<150°C)

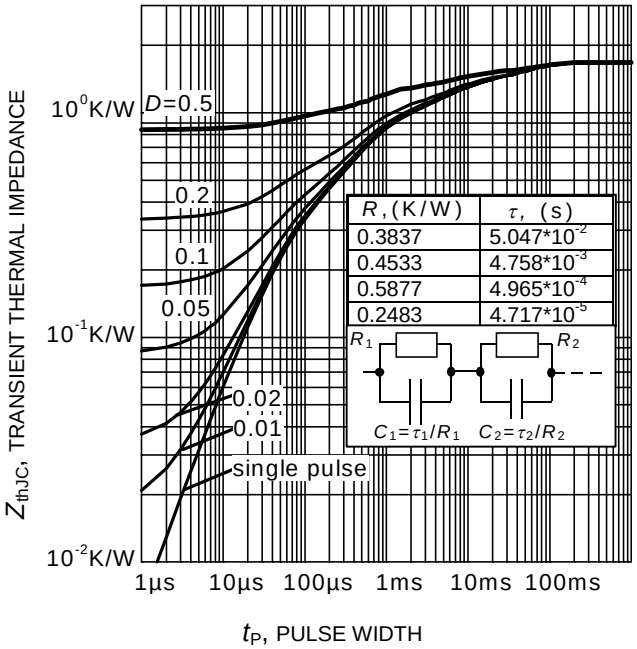
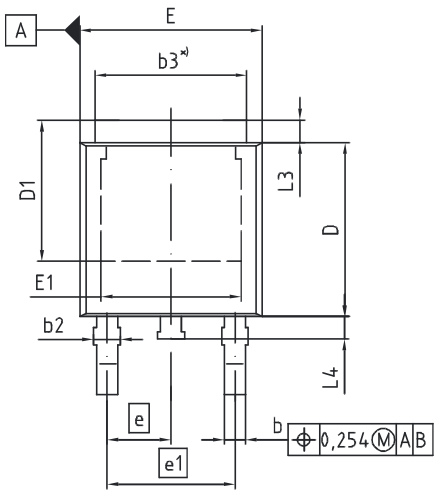
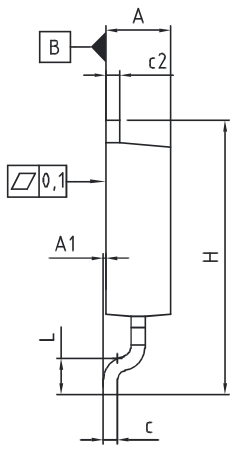
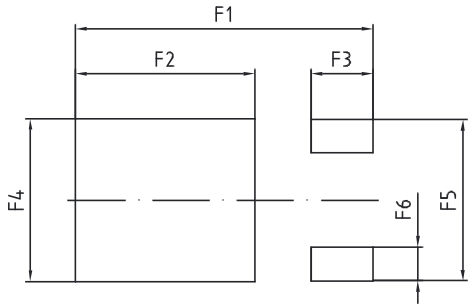


Figure 21. IGBT transient thermal impedance
($D = t_p / T$)

PG-TO252-3







*) mold flash not included

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29 (BSC)		0.090 (BSC)	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.60		0.417	
F2	6.40		0.252	
F3	2.20		0.087	
F4	5.80		0.228	
F5	5.76		0.227	
F6	1.20		0.047	

DOCUMENT NO.	Z8B00003328
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EUROPEAN PROJECTION	
ISSUE DATE	16-02-2011
REVISION	04

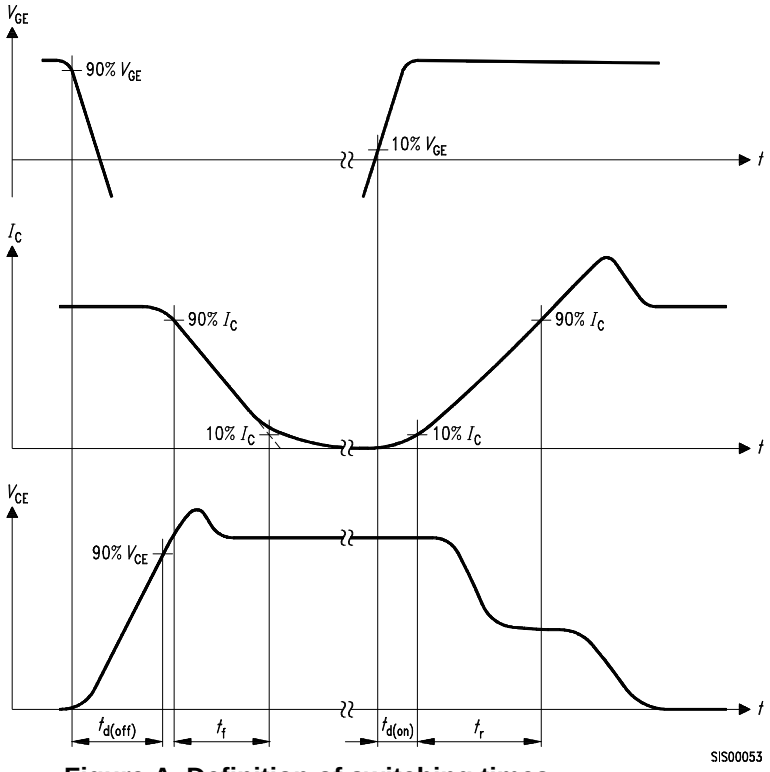


Figure A. Definition of switching times

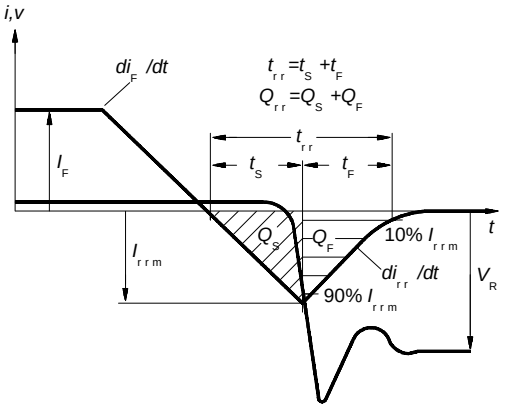


Figure C. Definition of diodes switching characteristics

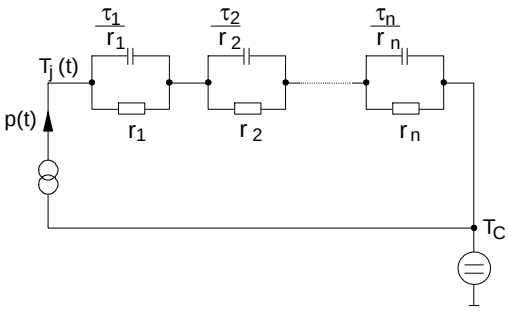


Figure D. Thermal equivalent circuit

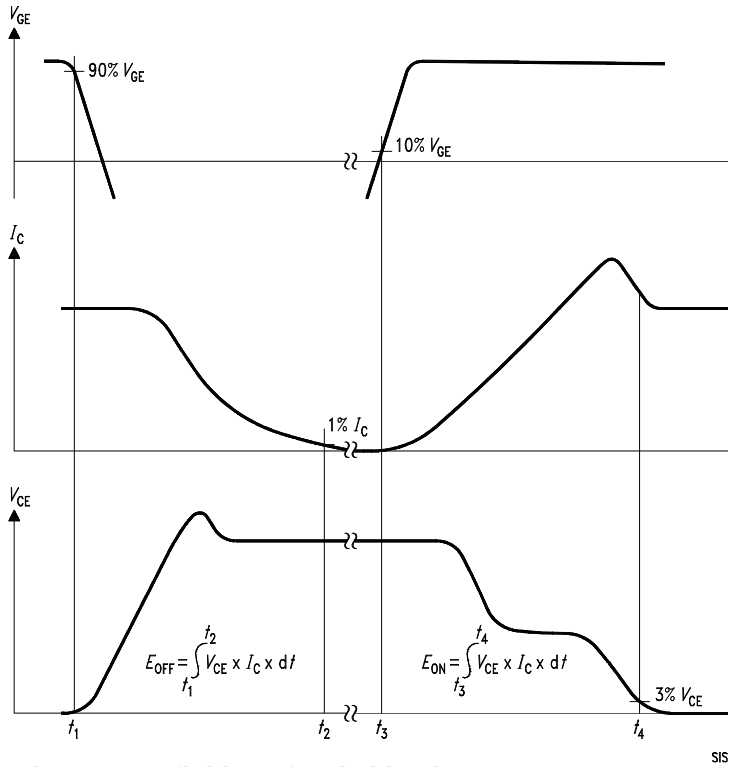


Figure B. Definition of switching losses

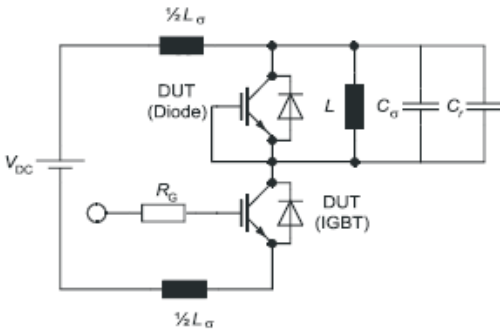


Figure E. Dynamic test circuit
Parasitic inductance L_σ,
Parasitic capacitor C_σ,
Relief capacitor C_r
(only for ZVT switching)

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